

MOS FIELD EFFECT TRANSISTOR 2SK3755

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3755 is N-channel MOS Field Effect Transistor designed for high current switching applications.

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3755	Isolated TO-220

FEATURES

- Super low on-state resistance

$R_{DS(on)1} = 12 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 23 \text{ A)}$

$R_{DS(on)2} = 18 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.5 \text{ V, } I_D = 23 \text{ A)}$

- Low C_{iss} : $C_{iss} = 1200 \text{ pF TYP.}$
- Built-in gate protection diode

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

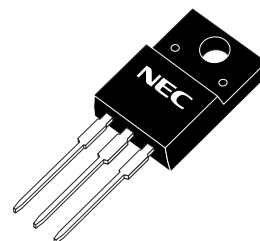
Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	40	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 45	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	± 140	A
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_{T1}	24	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_{T2}	2.0	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	$-55 \text{ to } +150$	$^\circ\text{C}$
Single Avalanche Current ^{Note2}	I_{AS}	23	A
Single Avalanche Energy ^{Note2}	E_{AS}	53	mJ
Repetitive Avalanche Energy ^{Note3}	E_{AR}	53	mJ

Notes 1. $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

2. Starting $T_{ch} = 25^\circ\text{C}$, $V_{DD} = 20 \text{ V}$, $R_G = 25 \Omega$, $V_{GS} = 20 \rightarrow 0 \text{ V}$

3. $I_{AR} \leq 23 \text{ A}$, $T_{ch} \leq 150^\circ\text{C}$

(Isolated TO-220)



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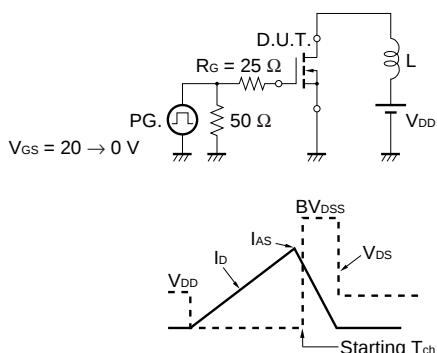
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ELECTRICAL CHARACTERISTICS (T_A = 25°C)

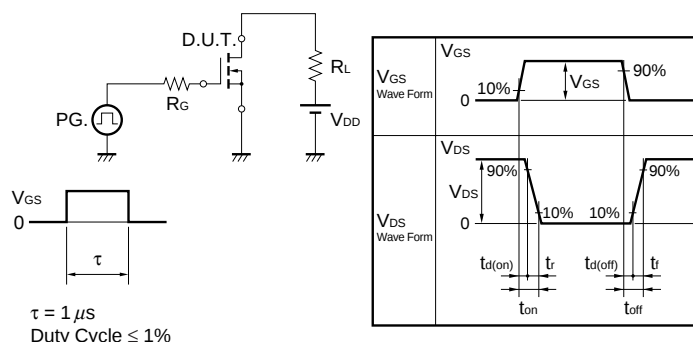
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V			10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.5	2.0	2.5	V
Forward Transfer Admittance ^{Note}	y _{fs}	V _{DS} = 10 V, I _D = 23 A	12	25		S
Drain to Source On-state Resistance ^{Note}	R _{DS(on)1}	V _{GS} = 10 V, I _D = 23 A		9.7	12	mΩ
	R _{DS(on)2}	V _{GS} = 4.5 V, I _D = 23 A		12.9	18	mΩ
Input Capacitance	C _{iss}	V _{DS} = 10 V		1200		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		330		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		120		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 20 V, I _D = 23 A		10		ns
Rise Time	t _r	V _{GS} = 10 V		4		ns
Turn-off Delay Time	t _{d(off)}	R _G = 0 Ω		35		ns
Fall Time	t _f			5		ns
Total Gate Charge	Q _G	V _{DD} = 32 V		25.5		nC
Gate to Source Charge	Q _{GS}	V _{GS} = 10 V		4.2		nC
Gate to Drain Charge	Q _{GD}	I _D = 45 A		7.1		nC
Body Diode Forward Voltage ^{Note}	V _{F(S-D)}	I _F = 45 A, V _{GS} = 0 V		0.98	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 45 A, V _{GS} = 0 V		29		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100 A/μs		30		nC

Note Pulsed

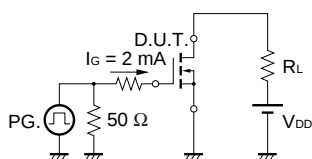
TEST CIRCUIT 1 AVALANCHE CAPABILITY



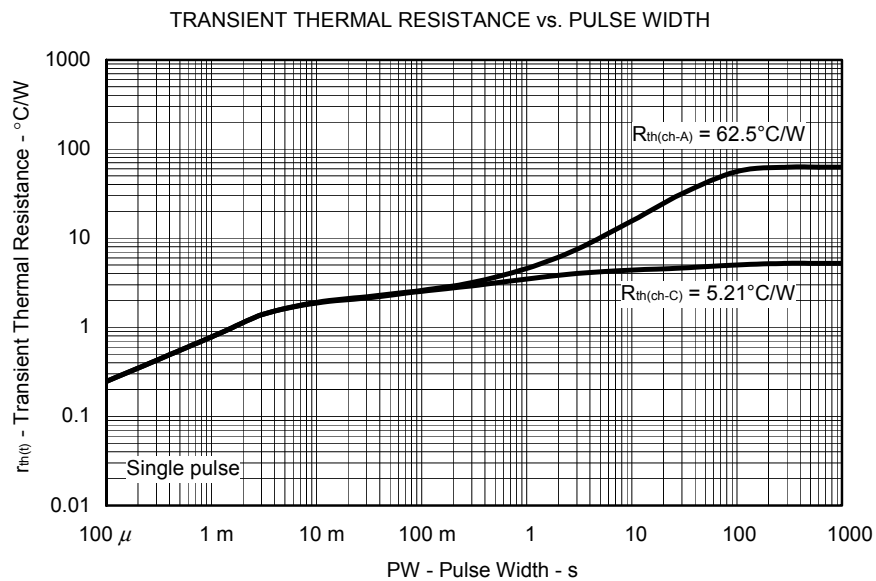
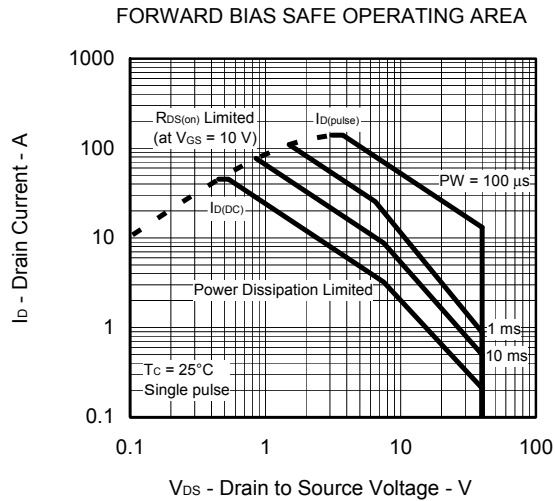
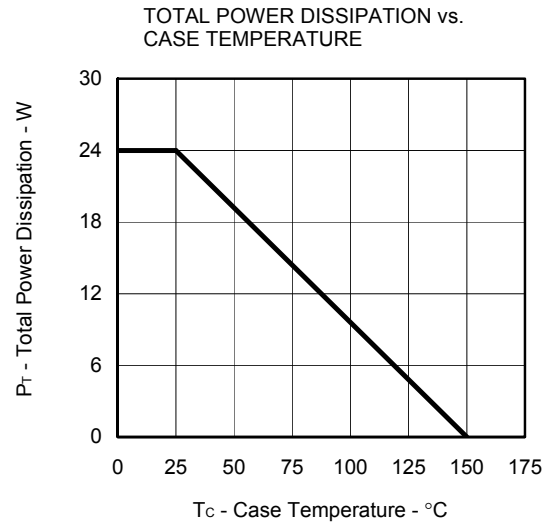
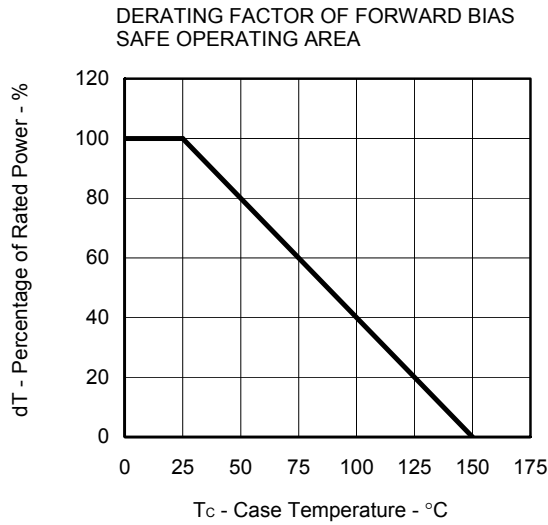
TEST CIRCUIT 2 SWITCHING TIME



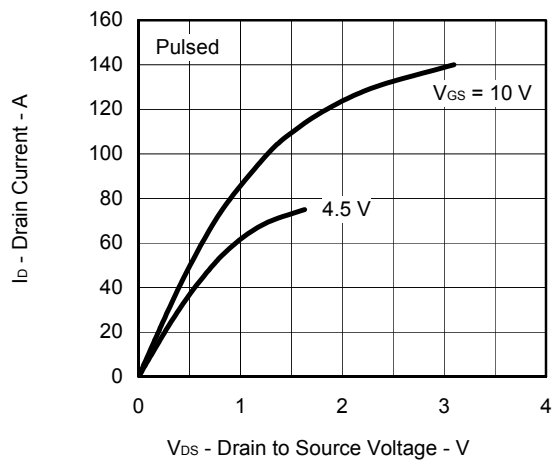
TEST CIRCUIT 3 GATE CHARGE



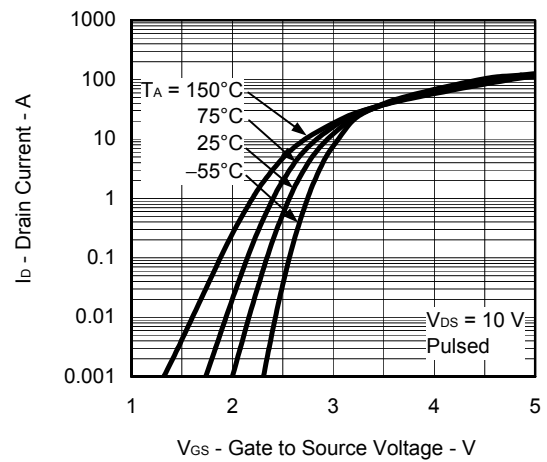
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)



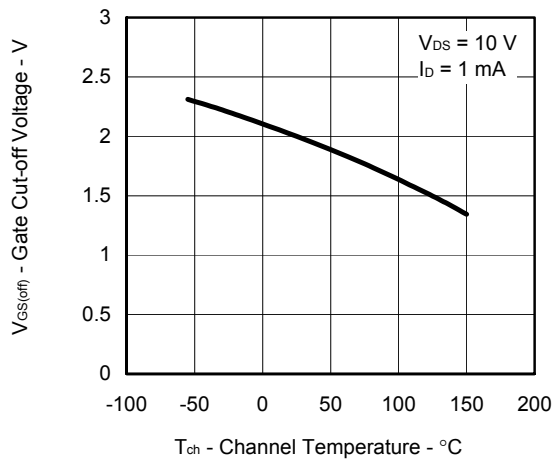
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



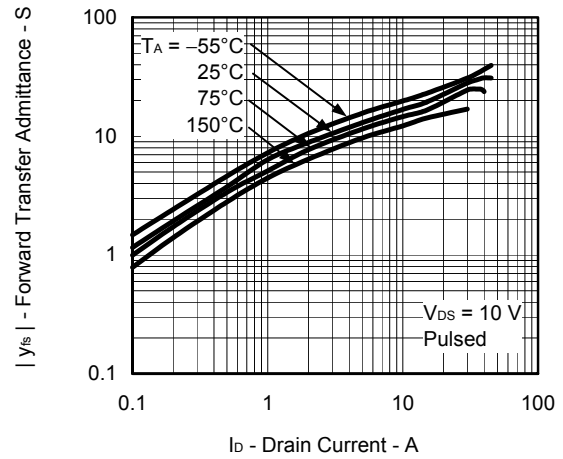
FORWARD TRANSFER CHARACTERISTICS



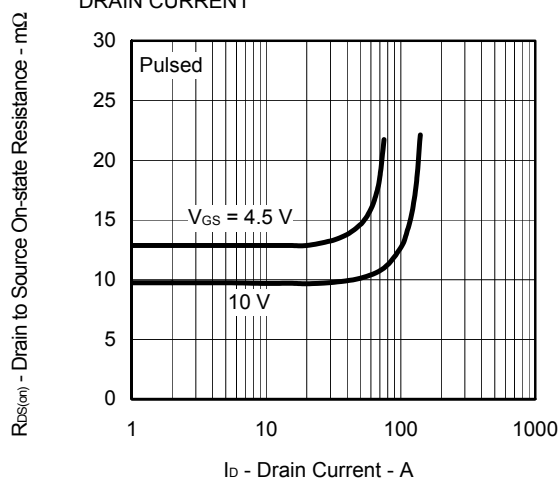
GATE CUT-OFF VOLTAGE vs.
CHANNEL TEMPERATURE



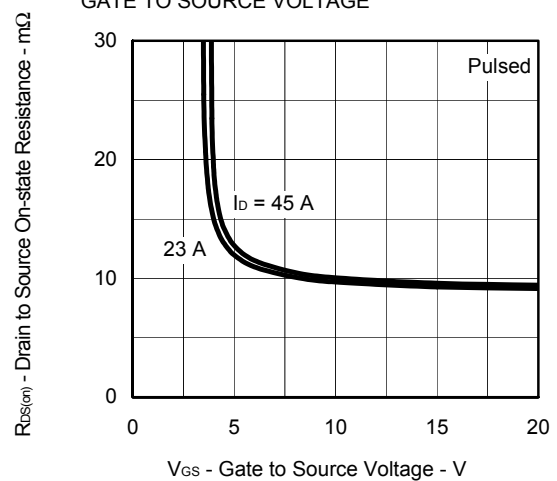
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



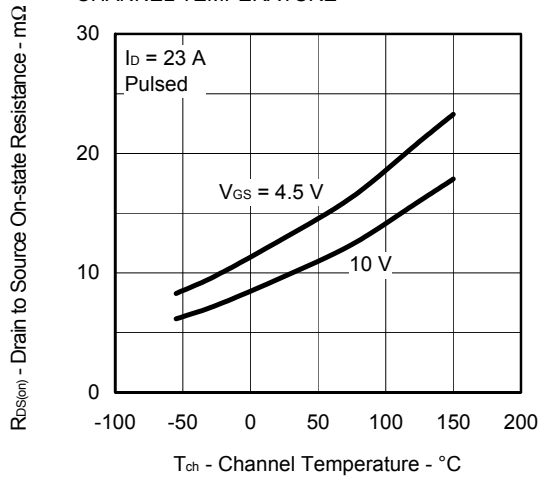
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENT



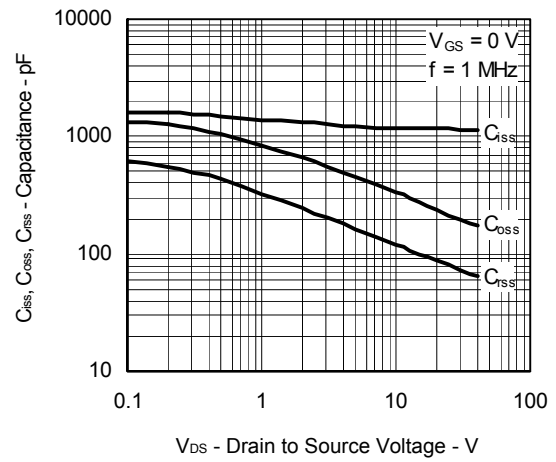
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



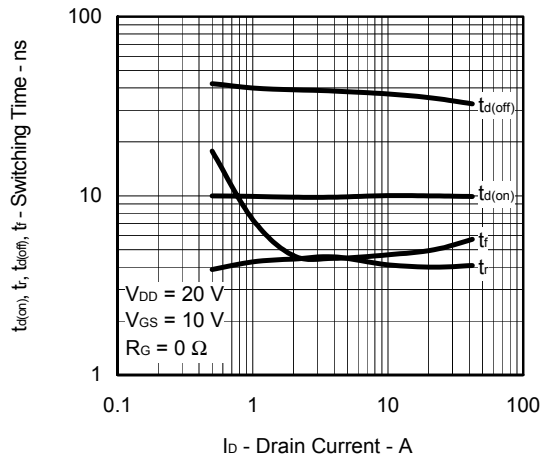
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



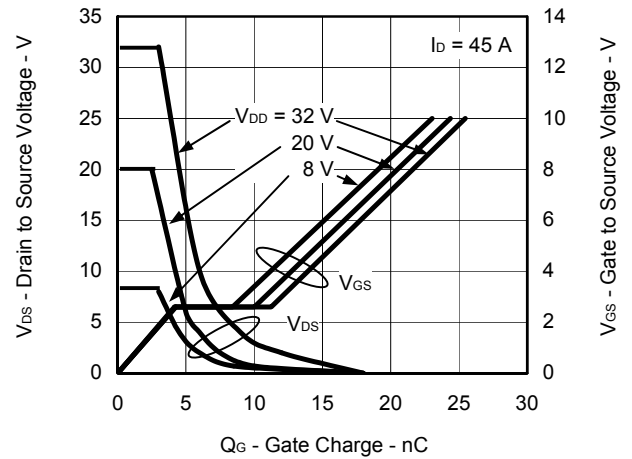
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



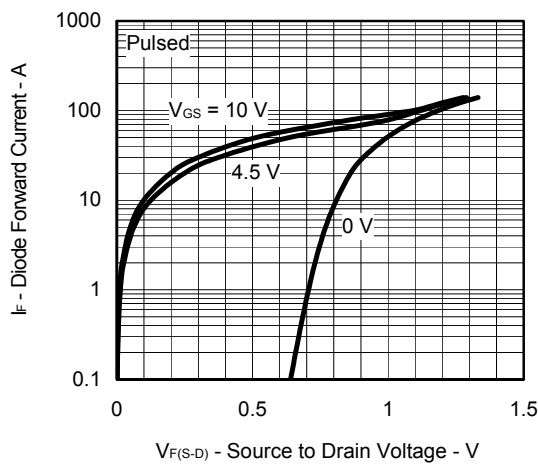
SWITCHING CHARACTERISTICS



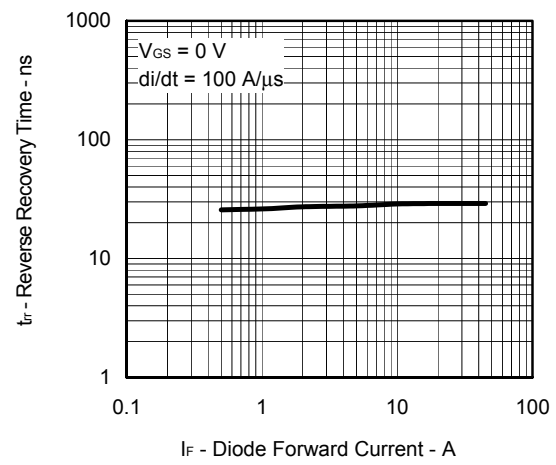
DYNAMIC INPUT/OUTPUT CHARACTERISTICS

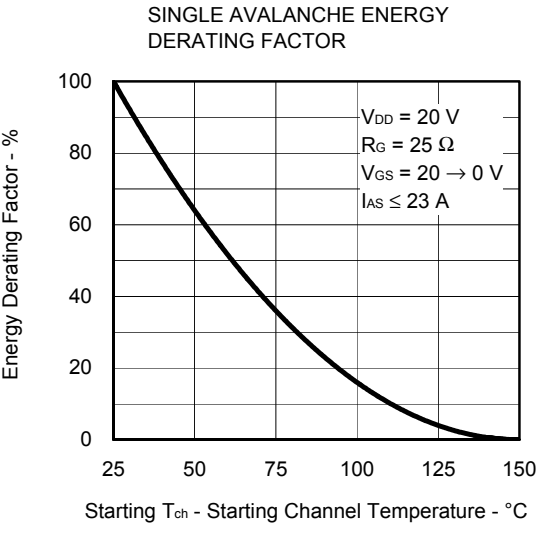
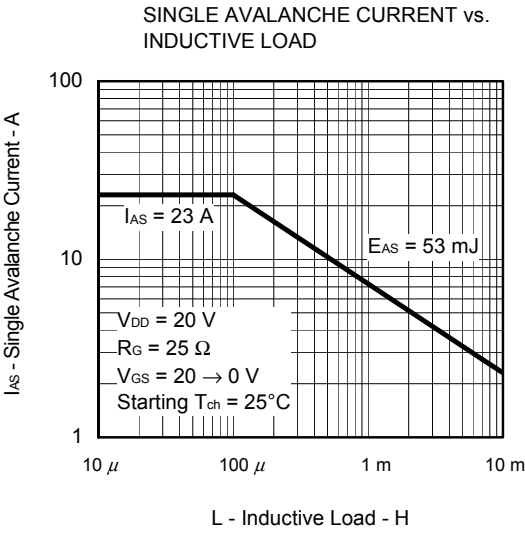


SOURCE TO DRAIN DIODE FORWARD VOLTAGE



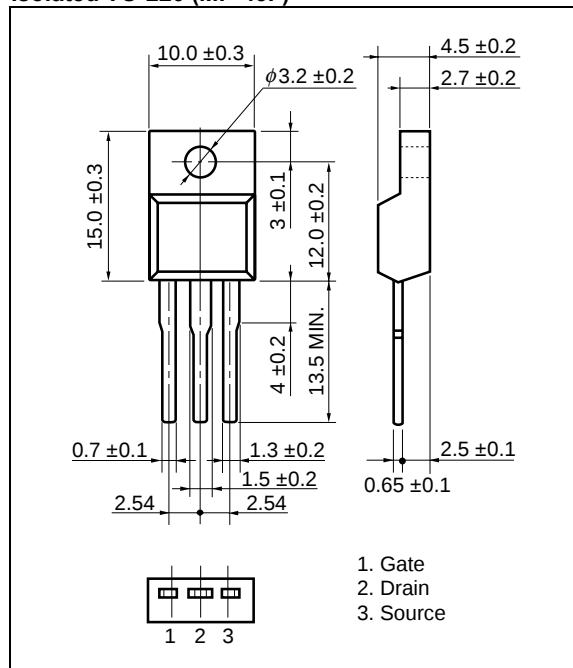
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



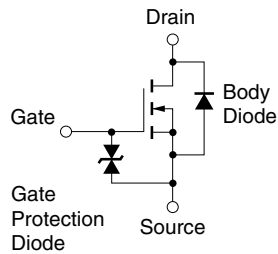


PACKAGE DRAWING (Unit: mm)

Isolated TO-220 (MP-45F)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD.

When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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